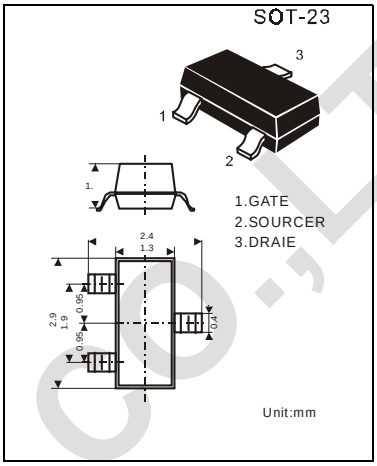
WEJ®

RoHS

BCX20LT1

NPN EPITAXIAL SILICON TRANSISTOR

GENERAL PURPOSE TRANSISTORS



ABSOLUTE MAXIMUM RATINGS at Ta=25℃

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	30	V
Collector-Emitter Voltage	Vceo	25	V
Emitter-Base Voltage	Vebo	5.0	V
Collector Current	Ic	500	mA
Total Device Dissipation FR-5 Board(1) Ta=25℃ Derate above 25℃	P_D	225 1.8	mw mW/℃
Total Device Dissipation Alumina Substrate,(2) Ta=25℃ Derate above 25℃	P_D	300 2.4	mw mW/℃
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55-150	℃

ELECTRICAL CHARACTERISTICS at Ta=25℃

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Voltage	V(BR)ceo	25			V	Ic=10mA Ib=0
Collector-Emitter Voltage	V(BR)ces	30			V	Ic=10uA Ic=0
Emitter Cutoff Current	Iebo			10	uA	Veb=5V Ic=0
Collector Cutoff Current	Icbo			100 5.0	nA uA	Vcb=20V Ie=0 Vcb=20V Ie=0 T_A=150℃
DC Current Gain	H_{FE}	100 70 40		600		Vce=1.0V Ic=-100mA Vce=1.0V Ic=-300mA Vce=1.0V Ic=-500mA
Collector-Emitter Saturation Voltage	Vce(sat)			620	mV	Ic=-500mA Ib=-50mA
Base-Emitter Saturation Voltage	Vbe(on)		1.2		V	Vbe=1V Ic=500mA

* 1.Total Device Dissipation : FR=1x0.75x0.062in .
2.Alumina=0.4 x 0.3 x 0.024in.99.5% alumina

DEVICE MARKING:

BCX20LT1=U2